

Highly efficient red electrophosphorescence from a solution-processed zwitterionic cyclometalated iridium(III) complex

Cite as: Appl. Phys. Lett. **91**, 211106 (2007); <https://doi.org/10.1063/1.2809375>

Submitted: 28 May 2007 • Accepted: 22 October 2007 • Published Online: 21 November 2007

Younghun Byun, Yi-Yeol Lyu, Rupasree Ragini Das, et al.



View Online



Export Citation

ARTICLES YOU MAY BE INTERESTED IN

Organic electroluminescent diodes

Applied Physics Letters **51**, 913 (1987); <https://doi.org/10.1063/1.98799>

Very high-efficiency green organic light-emitting devices based on electrophosphorescence

Applied Physics Letters **75**, 4 (1999); <https://doi.org/10.1063/1.124258>

Hole-transporting interlayers for improving the device lifetime in the polymer light-emitting diodes

Applied Physics Letters **89**, 123505 (2006); <https://doi.org/10.1063/1.2345239>



A new approach to low-level measurements of nanostructures
Read our technical note

[Download Now](#)

 Lake Shore
CRYOTRONICS

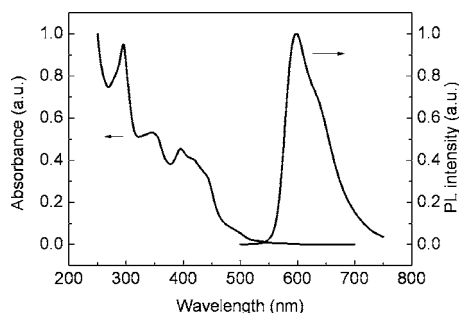


FIG. 2. UV and PL spectra of $(\text{piq})_2\text{Ir}^+[\text{BP}(\text{O}^-)(\text{OH})]$ in CHCl_3 .

angle of 76.02° and repulsion between the two oxygen atoms at 5,5'-positions. Substantiated by the dihedral angles of N3–C35–C36–N4, C34–C35–C36–C37, and O1–C34–C37–O2 are -11.5° , -17.6° , and -30.9° , respectively, indicating repulsion between the two oxygen atoms at ortho positions. It is interesting to note that only one hydrogen atom from the two hydroxy groups was removed under the reaction condition, which gives a charge-neutral zwitterionic iridium complex. Strong intramolecular hydrogen bonding is suggested by very short O1–O2 and averaged C–O distances of 2.392 and 1.307 Å, respectively. In the final refinement of the structure of $(\text{piq})_2\text{Ir}^+[\text{BP}(\text{O}^-)(\text{OH})]$, one hydrogen atom is automatically generated onto O1 atom with a distance of 0.821 Å and H–O2 distance of 1.701 Å. The strong coordination ability of N \wedge N ligand and the stability of the O1–H \cdots O2 hydrogen bond may be the driving force for the formation of zwitterionic iridium complex. Despite the easy availability of O $^-$ coordinating site, this is an unusual example of a nonoxygen coordinated Ir(III) complex.

The UV/visible absorption and emission spectra of $(\text{piq})_2\text{Ir}^+[\text{BP}(\text{O}^-)(\text{OH})]$ in CHCl_3 solution are shown in Fig. 2. The bands below 360 nm can be assigned to the spin-allowed $^1\pi\text{-}\pi^*$ transition of cyclometalated ligand, the broadband of 380–450 nm and the band at 492 nm can be assigned to metal ligand charge transfer ($^1\text{MLCT}$) and $^3\text{MLCT}$, respectively. The complex shows the peak emission at 606 nm. It is worthwhile to point out that the complex $[\text{Ir}(\text{piq})_2(\text{bpy})]^+(\text{PF}_6)^-$ is reported⁶ to have a peak emission at 586 nm, whereas the presence of the two OH groups in the 5,5'-positions of the bipyridine ligand in the complex $(\text{piq})_2\text{Ir}^+[\text{BP}(\text{O}^-)(\text{OH})]$ redshifts the emission to 606 nm.

Poly(N-vinyl carbazole) (PVK) was used as the host because its emission spectrum overlaps with the absorption spectrum of $(\text{piq})_2\text{Ir}^+[\text{BP}(\text{O}^-)(\text{OH})]$. PVK is known to be a preferentially hole transporting material. Therefore, we blended the PVK with an electron transporting material, 2-tert-butylphenyl-5-biphenyl-1,3,4-oxadiazole (PBD) to enable the host to transport both electrons and holes. Solution-processed electrophosphorescent devices were fabricated by doping the emitter ($(\text{piq})_2\text{Ir}^+[\text{BP}(\text{O}^-)(\text{OH})]$) into the mixed host of PVK and PBD (40 wt %). Poly(3,4-ethylenedioxythiophene)-polystyrene sulfonate (PEDOT:PSS) as a hole injecting layer and 2,2',2''-(1,3,5-benzinetriyl)-tris(1-phenyl-1-H-benzimidazole) (TPBI) as an electron-transporting/hole-blocking layer were employed. We optionally employed poly[2,7-(9,9-di-*n*-octylfluorene)-alt-(1,4-phenylene)-[(4-sec-butylphenyl)amino]-1,4-phenylene] (TFB) as a hole transporting inter-

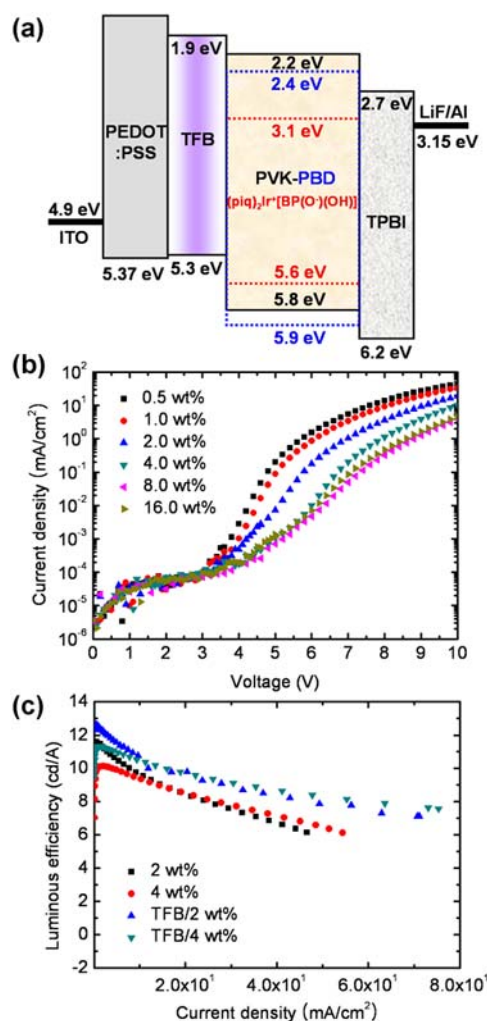


FIG. 3. (Color online) The device structure and the device characteristics of red electrophosphorescent devices using $(\text{piq})_2\text{Ir}^+[\text{BP}(\text{O}^-)(\text{OH})]$ as a dopant in PVK-PBD (40 wt %) host with varying dopant concentrations with or without a TFB interlayer. (a) The device structure, (b) current-density vs voltage characteristics of the luminous efficiency of red electrophosphorescent devices using $(\text{piq})_2\text{Ir}^+[\text{BP}(\text{O}^-)(\text{OH})]$ as a dopant in PVK-PBD (40 wt %) host with varying dopant concentrations. (c) Luminous efficiency vs current-density with varying dopant concentrations (2 and 4 wt %) with or without a TFB interlayer.

layer between PEDOT:PSS and the emitting layer (EML) in order to improve the hole transport to the EML and block electrons at the TFB/EML interface. The device structure and energy levels of each layer are shown in Fig. 3(a). The highest occupied molecular orbital (HOMO) and lowest unoccupied molecular orbital levels (LUMO) of PVK are -5.8 and -2.2 eV, respectively.¹¹ The HOMO and LUMO of PBD are -5.9 and -2.4 eV, respectively.¹² In order to reduce the hole injection barrier, we used our reformulated PEDOT:PSS by adding a low molecular weight PSS (MW=48 000 g/mol) to the conventional PEDOT:PSS (Baytron P AI4083, PSS MW =0490000 g/mol) having a higher work function of 5.37 eV.

Since the HOMO and LUMO of the $(\text{piq})_2\text{Ir}^+[\text{BP}(\text{O}^-)(\text{OH})]$ are -5.6 and -3.1 eV, respectively, holes or electrons can be trapped by $(\text{piq})_2\text{Ir}^+[\text{BP}(\text{O}^-)(\text{OH})]$, and, subsequently, can recombine directly on the dopant.¹³ In these devices, even at a low concentration of the dopant, the charge trapping can hugely reduce the mobility of the emitting host. It has been reported that the charge carrier mobilities in PVK are drastically reduced almost by three orders of

TABLE I. The performance of the devices using $(\text{piq})_2\text{Ir}^+[\text{BP}(\text{O}^-)(\text{OH})]$ doped into a PVK-PBD host as an emitting layer (EML) in the structure of ITO/PEDOT:PSS/EML/TPBI/LiF/Al and ITO/PEDOT:PSS/TFB/EML/TPBI/LiF/Al.

$(\text{piq})_2\text{Ir}^+[\text{BP}(\text{O}^-)(\text{OH})]$ in PVK-PBD (40%)	Luminous efficiency (cd/A)	External quantum efficiency (%)	CIE at 100 cd/m ²	Turn-on voltage (V)
0.5%	2.97	2.15	0.48,0.32	4.0
1%	9.25	6.48	0.59,0.38	4.2
2%	11.61	8.01	0.61,0.38	4.4
4%	10.15	7.16	0.62,0.38	5.6
8%	7.83	6.13	0.63,0.38	5.8
16%	5.31	5.69	0.66,0.34	5.8
TFB/2%	12.62	8.60	0.61,0.38	4.0
TFB/4%	11.33	8.76	0.63,0.37	4.6
TFB/8%	8.70	7.96	0.64,0.36	5.2

magnitude by the addition of a small amount of N,N' -diphenyl- N,N' -bis(3-methylphenyl)-[1,1'-biphenyl]-4,4'-diamine (TPD).¹⁴ We also observed similar huge reduction of the current densities in the $(\text{piq})_2\text{Ir}^+[\text{BP}(\text{O}^-)(\text{OH})]$ devices without a TFB interlayer, as Fig. 3(b) shows. The current densities of the devices drastically decrease from 0.5 to 4 wt % concentration owing to the charge trapping which is then saturated upon increasing the doping concentration up to 16 wt % above which the hopping transport via dopants tends to be more dominated.

Table I summarizes the performance of the devices using $(\text{piq})_2\text{Ir}^+[\text{BP}(\text{O}^-)(\text{OH})]$ doped into a PVK-PBD host as EML in the structure of ITO/PEDOT:PSS/EML/TPBI/LiF/Al and ITO/PEDOT:PSS/TFB/EML/TPBI/LiF/Al with varying dopant concentrations. As for the former devices, at 2 wt % $(\text{piq})_2\text{Ir}^+[\text{BP}(\text{O}^-)(\text{OH})]$ concentration, the LE reached the maximum. The decrease in LE at higher doping concentrations probably results from aggregation and self-quenching of the $(\text{piq})_2\text{Ir}^+[\text{BP}(\text{O}^-)(\text{OH})]$. Only 2 wt % doping of the guest into the PVK-PBD (40 wt %) host resulted in very high LE of 11.61 cd/A (8.01% ph/el), which is a quite high LE comparable to the best performance of solution-processed red phosphorescent devices.¹⁵

The device efficiency was further improved by introducing the hole-transporting interlayer (TFB) (HOMO: -5.3 eV, LUMO: -1.9 eV) between the PEDOT:PSS and the EML up to 12.62 cd/A (8.60% ph/el), as Fig. 3(c) shows. The TFB interlayer plays roles in transporting holes from the PEDOT:PSS layer and blocking electrons at the TFB/emitter interface,^{11,16} which results in a more balanced electron-hole recombination and confinement of exciton in the EML. When the interlayer was employed, the rolling-off phenomena of the device efficiency at high currents were reduced which may imply that the exciton quenching by PEDOT:PSS can be removed by the interlayer at high currents.¹⁶ Therefore, this indicates that the roll-off phenomena at high electric fields in phosphorescent OLEDs can be caused by the exciton quenching by adjacent layers such as anode, cathode, and PEDOT:PSS, as well as triplet-triplet annihilation.^{3,17} We measured the transient electroluminescence of the device using 4 wt % $(\text{piq})_2\text{Ir}^+[\text{BP}(\text{O}^-)(\text{OH})]$ in PVK-PBD without the TFB interlayer with 6 V step voltage pulse and 10 Hz fre-

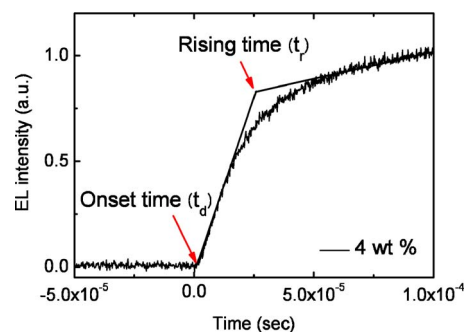


FIG. 4. (Color online) The transient electroluminescence of ITO/PEDOT:PSS/4 wt % $(\text{piq})_2\text{Ir}^+[\text{BP}(\text{O}^-)(\text{OH})]$ in PVK-PBD/TPBI/LiF/Al

quency which provided a fast response time of the devices (the EL onset time (t_d): $1.6 \mu\text{s}$, the rising time (t_r): $25.9 \mu\text{s}$) (see Fig. 4).

In summary, an iridium(III) complex, $(\text{piq})_2\text{Ir}^+[\text{BP}(\text{O}^-)(\text{OH})]$ was synthesized and the exact configuration of $(\text{piq})_2\text{Ir}^+[\text{BP}(\text{O}^-)(\text{OH})]$ was confirmed using the single-crystal x-ray diffraction analysis. $\text{BP}(\text{OH})_2$ can act as a bidentate ligand ($\text{N}\wedge\text{N}$ or $\text{N}\wedge\text{O}$ fashion) or as a bridging tetradentate ligand to two metal centers and can afford various zwitterionic metal complexes. The high solubility in organic solvents enables solution process for the device fabrication. We demonstrate high-efficiency red electrophosphorescent devices (12.62 cd/A) with fast response time using $(\text{piq})_2\text{Ir}^+[\text{BP}(\text{O}^-)(\text{OH})]$ as the dopant in the mixed host of PVK and PBD.

¹M. A. Baldo, D. F. O'Brien, Y. You, A. Shoustikov, S. Sibley, M. E. Thompson, and S. R. Forrest, *Nature (London)* **395**, 151 (1998).

²E. Holder, B. M. W. Langeveld, and U. S. Schubert, *Adv. Mater. (Weinheim, Ger.)* **17**, 1109 (2005); Y.-J. Su, H.-L. Huang, C.-L. Li, C.-H. Chien, U.-T. Tao, P.-T. Chou, S. Datta, and R.-S. Liu, *ibid.* **15**, 884 (2003).

³C. Adachi, M. A. Baldo, and S. R. Forrest, *J. Appl. Phys.* **87**, 8049 (2000).

⁴M. A. Baldo, S. Lamansky, P. E. Burrows, M. E. Thompson, and S. R. Forrest, *Appl. Phys. Lett.* **75**, 4 (1999).

⁵P. Coppo, E. A. Plummer, and L. De Cola, *Chem. Commun. (Cambridge)* **2004**, 17444.

⁶Q. Zhao, S. Liu, M. Shi, C. Wang, M. Yu, L. Li, F. Li, T. Yi, and C. Huang, *Inorg. Chem.* **45**, 6152 (2001); W.-Y. Wong, G.-J. Zhou, X.-M. Yu, H.-S. Kwok, and Z. Lin, *Adv. Funct. Mater.* **17**, 315 (2007).

⁷J. Slinker, D. Bernard, P. L. Houston, H. D. Abruna, S. Bernhard, and G. G. Malliaras, *Chem. Commun. (Cambridge)* **2003**, 2392.

⁸S. Lamansky, P. Djurovich, D. Murphy, F. Abdel-Razzaq, R. Kwong, I. Tsyba, M. Bortz, B. Mui, R. Bau, and M. E. Thompson, *Inorg. Chem.* **40**, 1704 (2001).

⁹R. Urban, R. Krämer, S. Mihan, K. Polborn, B. Wagner, and W. Beck, *J. Organomet. Chem.* **517**, 191 (1996); F. Neve and A. Crispini, *Pap. Conv. Am. Nurs. Assoc.* **2000**, 1039.

¹⁰J. Lipkowski, A. Grabowska, J. Waluk, G. Calestani, and B. A. Hess, Jr., *J. Crystallogr. Spectrosc. Res.* **22**, 563 (1992).

¹¹T.-W. Lee, M.-G. Kim, S. Y. Kim, S. H. Park, O. Kwon, and T. Noh, *Appl. Phys. Lett.* **89**, 123505 (2006).

¹²J. Kido, H. Shionoya, and K. Nagai, *Appl. Phys. Lett.* **67**, 2281 (1995).

¹³X. Gong, J. C. Ostrowski, D. Moses, G. C. Bazan, and A. J. Heeger, *Adv. Funct. Mater.* **13**, 439 (2003).

¹⁴D. M. Pai, J. F. Yanus, and M. Stolka, *J. Phys. Chem.* **88**, 4714 (1984).

¹⁵X. Yang, D. C. Muller, D. Neher, and K. Meerholtz, *Adv. Mater. (Weinheim, Ger.)* **18**, 948 (2006).

¹⁶J.-S. Kim, R. H. Friend, I. Grizzi, and J. H. Burroughes, *Appl. Phys. Lett.* **87**, 023506 (2005).

¹⁷C. Adachi, M. A. Baldo, M. E. Thompson, and S. R. Forrest, *J. Appl. Phys.* **90**, 5048 (2001).